

Negative Output Flyback Pulse Width Modulator

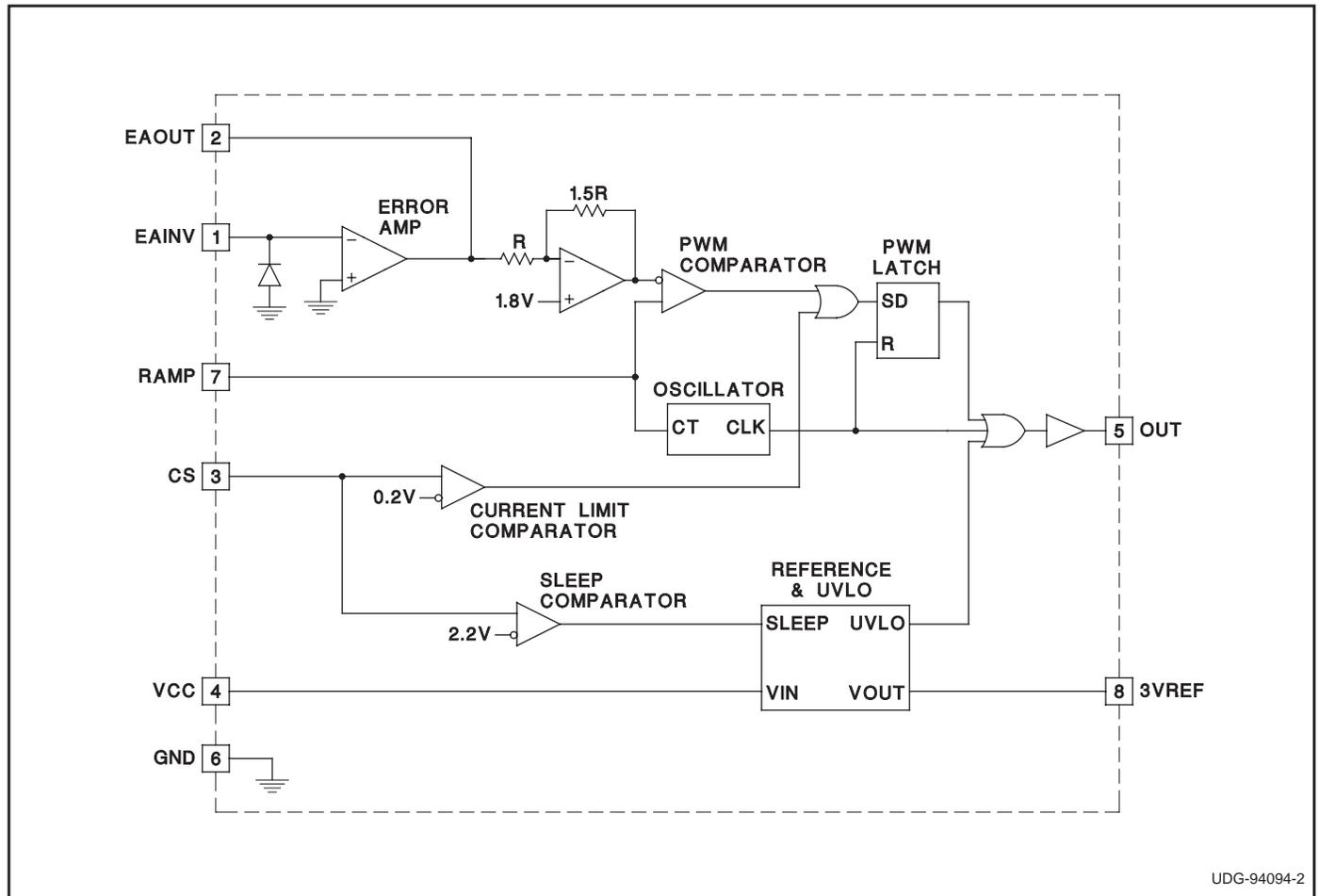
FEATURES

- Simple Single Inductor Flyback PWM for Negative Voltage Generation
- Drives External PMOS Switch
- Contains UVLO Circuit
- Includes Pulse-by-Pulse Current Limit
- Low 50mA Sleep Mode Current

DESCRIPTION

The UC3572 is a negative output flyback pulse width modulator which converts a positive input voltage to a regulated negative output voltage. The chip is optimized for use in a single inductor negative flyback switching converter employing an external PMOS switch. The block diagram consists of a precision reference, an error amplifier configured for voltage mode operation, an oscillator, a PWM comparator with latching logic, and a 0.5A peak gate driver. The UC3572 includes an undervoltage lockout circuit to insure sufficient input supply voltage is present before any switching activity can occur, and a pulse-by-pulse current limit. Output current can be sensed and limited to a user determined maximum value. The UVLO circuit turns the chip off when the input voltage is below the UVLO threshold. In addition, a sleep comparator interfaces to the UVLO circuit to turn the chip off. This reduces the supply current to only 50 μ A, making the UC3572 ideal for battery powered applications.

BLOCK DIAGRAM



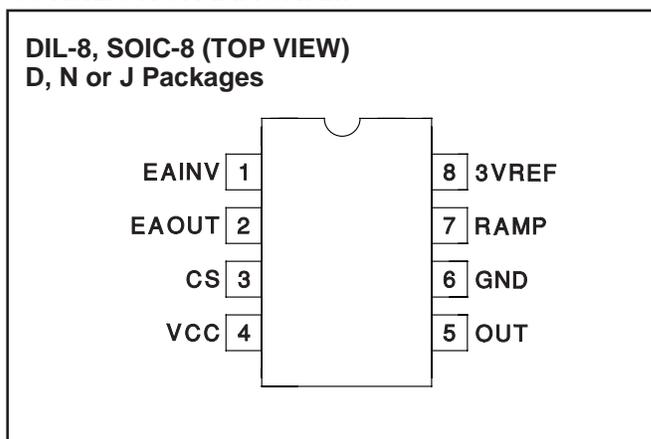
UDG-94094-2

ABSOLUTE MAXIMUM RATINGS

VCC	35V
EAINV	-0.6V to VCC
IEAOUT	25mA
RAMP	-0.3V to 4V
CS	-0.3V to VCC
I _{out}	-0.7A to 0.7A
I _{3VREF}	-15mA
Storage Temperature	-65°C to +150°C
Junction Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 sec.)	+300°C

Currents are positive into, negative out of the specified terminal. Consult Packaging Section of Databook for thermal limitations and considerations of packages.

CONNECTION DIAGRAM



	Temperature Range	Available Packages
UC1572	-55°C to +125°C	J
UC2572	-40°C to +85°C	D, N or J
UC3572	0°C to +70°C	D or N

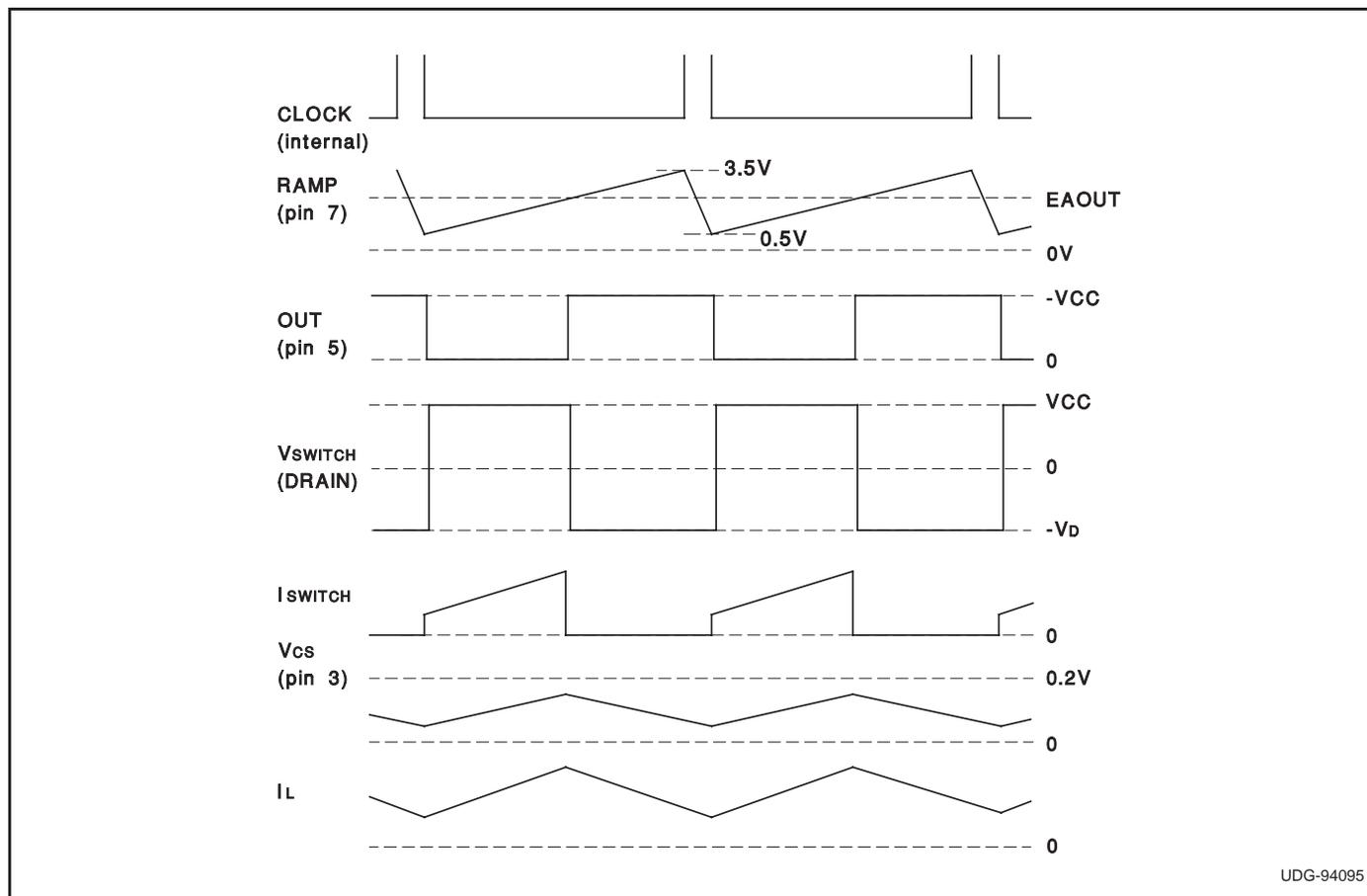
ELECTRICAL CHARACTERISTICS

Unless otherwise specified, VCC = 5V, CT = 680pF, TA = TJ.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Reference Section					
3VREF		2.94	3	3.06	V
Line Regulation	VCC = 4.75 to 30V		1	10	mV
Load Regulation	I _{3VREF} = 0V to -5mA		1	10	mV
Oscillator Section					
Frequency	VCC = 5V to 30V	85	100	115	kHz
Error Amp Section					
EAINV	EAOUT = 2V	-10	0	10	mV
	IEANV = -1mA		-0.2	-0.9	V
IEAINV	EAOUT = 2V		-0.2	-1.0	μA
AVOL	EAOUT = 0.5V to 3V	65	90		dB
EAOUT High	EAINV = -100mV	3.6	4	4.4	V
EAOUT Low	EAINV = 100mV		0.1	0.2	V
IEAOUT	EAINV = -100mV, EAOUT = 2V	-350	-500		μA
	EAINV = 100mV, EAOUT = 2V	7	20		mA
Unity Gain Bandwidth	TJ = 25°C, F = 10kHz	0.6	1		MHz
Current Sense Comparator Section					
Threshold		0.195	0.215	0.235	V
Input Bias Current	CS = 0		-0.4	-1	μA
CS Propagation Delay			300		nS
Gate Drive Output Section					
OUT High Saturation	I _{OUT} = 0		0	0.3	V
	I _{OUT} = -10mA		0.7	1.5	V
	I _{OUT} = -100mA		1.5	2.5	V
OUT Low Saturation	I _{OUT} = 10mA		0.1	0.4	V
	I _{OUT} = 100mA		1.5	2.2	V

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PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Rise Time	TJ = 25°C, CLOAD = 1nF + 3.3 Ohms		30	80	nS
Fall Time	TJ = 25°C, CLOAD = 1nF + 3.3 Ohms		30	80	nS
Pulse Width Modulator Section					
Maximum Duty Cycle	EAINV = +100mV, VCC = 5V to 30V		92	96	%
Minimum Duty Cycle	EAINV = -100mV, VCC = 5V to 30V			0	%
Modulator Gain	EAOUT = 1.5V to 2.5V	45	55	65	%/V
Undervoltage Lockout Section					
Start Threshold		3.5	4.2	4.7	V
Hysteresis		100	200	300	mV
Sleep Mode Section					
Threshold		1.8	2.2	2.6	V
Supply Current Section					
IVCC	VCC = 5V, 30V		9	12	mA
	VCC = 30, CS = 3V		50	150	μA



PIN DESCRIPTIONS

3VREF: Precision 3V reference. Bypass with 100nF capacitor to GND.

CS: Current limit sense pin. Connect to a ground referenced current sense resistor in series with the flyback inductor. OUT will be held high (PMOS switch off) if CS exceeds 0.2V.

EAINV: Inverting input to error amplifier. Summing junction for 3VREF and VOUT sense. The non-inverting input of the error amplifier is internally connected to GND. This pin will source a maximum of 1mA.

EAOUT: Output of error amplifier. Use EAOUT and EAINV for loop compensation components.

GND: Circuit Ground.

OUT: Gate drive for external PMOS switch connected between VCC and the flyback inductor. OUT drives the gate of the PMOS switch between VCC and GND.

RAMP: Oscillator and ramp for pulse width modulator. Frequency is set by a capacitor to GND by the equation

$$F = \frac{1}{15k \cdot C_{RAMP}}$$

Recommended operating frequency range is 10kHz to 200kHz.

VCC: Input voltage supply to chip. Range is 4.75 to 30V. Bypass with a 1μF capacitor.

TYPICAL APPLICATION: +5V TO -12V FLYBACK CONVERTER

